

## 3-Phase 600V Gate Driver IC

### Description

SA2636 are full bridge drivers to control power devices like MOS-transistors or IGBTs in 3-phase systems with a maximum blocking voltage of +600 V.

The three independent drivers are controlled at the low-side using CMOS and LSTTL compatible signals, down to 3.3V logic.

SA2636 includes an under-voltage detection unit with hysteresis characteristic and over-current detection. The over-current level is adjusted by choosing the resistor value and the threshold level at pin ITRIP. Both error conditions (under-voltage and over-current) lead to a definite shut down of all six switches. An error signal is provided at the FAULTB open drain output pin. The blocking time after over-current can be adjusted with an RC-network at pin RCIN. Therefore, the resistor  $R_{RCIN}$  is optional.

SA2636 typical output current can be given with 300mA for pull-up and 600mA for pull down. Because of system safety reasons a 290ns dead time has been realized. The function of inputs EN and ITRIP can optionally be extended with over-temperature detection, using an external NTC resistor, diodes and resistor network.

### Feature

- Fully operate up to 600V
- Gate drive supply range from 10V to 20V
- Built-in dead-time protection
- Shoot-through protection
- Independent Enable/disable input and fault reporting
- Shut down all switches during error conditions
- Adjustable fault clear timing
- 3.3 V/5V/15V input logic compatible
- Tolerant to negative transient voltage, dV/dt immune
- Matched propagation delays for all channels
- Matched dead time
- -40°C to 125°C operating range
- SOP28 Package available

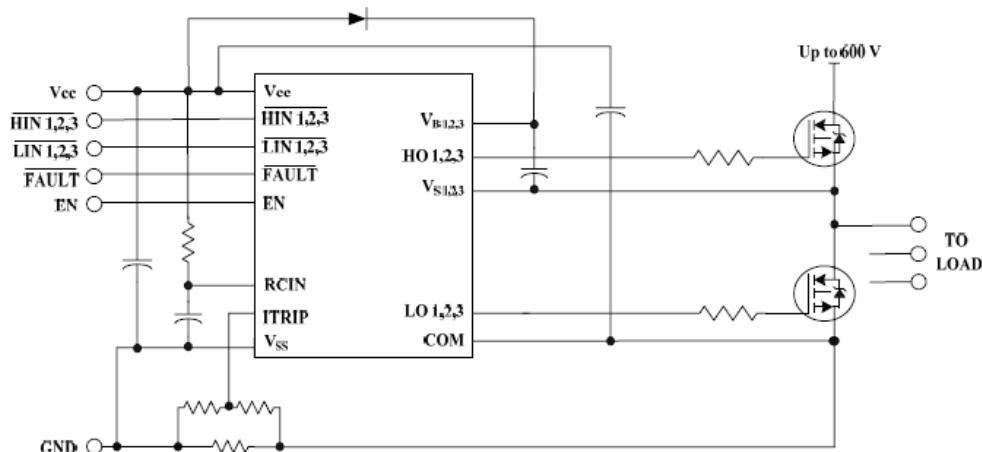
### Applications

- Servo drivers
- Industrial inverters
- Appliance motor driver

### Device Information

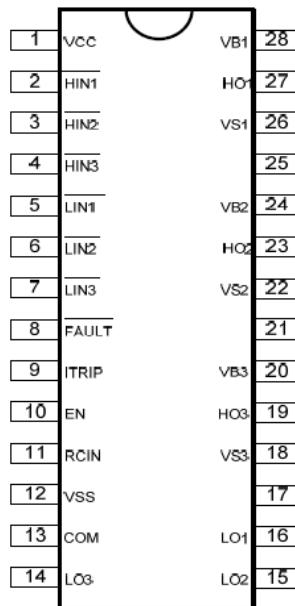
Part No.	Package	Quantity
SA2636	SOP28	1000/Reel

### SA2636 Simplified Circuit



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## Pin Configuration and Functions



NO.	NAME	TYPE	DESCRIPTION
1	VCC	P	Logic and low-side gate drivers power supply voltage
2,3,4	/HIN1,2,3	I	Logic input for high-side gate driver output (HO), out of phase.
5,6,7	/LIN1,2,3	I	Logic input for low-side gate driver output (LO), out of phase.
8	/FAULT	O	Indicates over-current (ITRIP) or low-side undervoltage lockout has occurred. Negative logic, open-drain output.
9	ITRIP	O	Analog input for overcurrent shutdown. When active, ITRIP shuts down outputs and activates FAULT and RCIN low. When ITRIP becomes inactive, FAULT stays active low for an externally set time $T_{FLTCLR}$ , then automatically becomes inactive (open-drain high impedance).
10	EN	I	Logic input to enable I/O functionality. I/O logic functions when ENABLE is high. No effect on FAULT and not latched.
11	RCIN	I	External RC network input used to define FAULT CLEAR delay, $T_{FLTCLR}$ , approximately equal to $R*C$ . When $RCIN > 8$ V, the FAULT pin goes back into open-drain high-impedance.
12	VSS	P	Logic ground
13	COM	P	Low-side gate drivers return
14,15,16	LO1,2,3	O	Low-side gate driver outputs
17,21,25	NC	NC	No connection
18,22,26	VS1,2,3	P	High-side floating supply return
19,23,27	HO1,2,3	O	High-side gate driver outputs
20,24,28	VB1,2,3	P	High-side floating supply

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### Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Definition	Symbol	Min	Max	Unit
High side floating supply voltage	$V_B$	-0.3	700	V
High side offset voltage	$V_S$	$V_B-25$	$V_B+0.3$	
High side floating output voltage	$V_{HO}$	$V_S-0.3$	$V_B+0.3$	
Low side and logic fixed supply voltage	$V_{CC}$	-0.3	25	
Low side output voltage	$V_{LO}$	-0.3	$V_{CC}+0.3$	
Input voltage LIN, HIN, ITRIP, EN	$V_{IN}$	-0.3	$V_{CC}+0.3$	
RCIN input voltage	$V_{RCIN}$	-0.3	$V_{CC}+0.3$	
FAULTB output voltage	$V_{FLT}$	-0.3	$V_{CC}+0.3$	
Allowable offset voltage slew rate	$dV_S/dt$		50	
Junction temperature	$T_J$	-40	150	$^{\circ}\text{C}$
Ambient temperature	$T_A$	-40	125	
Storage temperature	$T_{stg}$	-65	150	
Thermal resistance, junction to ambient	$\theta_{JA}$		78	$^{\circ}\text{C}/\text{W}$

### Recommended Operating Conditions

The input/output logic-timing diagram is shown in Fig. 1. For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute referenced to COM. The VS offset ratings are tested with all supplies biased at a 15 V differential.

Definition	Symbol	Min	Max	Unit
High side floating supply voltage	$V_B$	-0.3	600	V
High side offset voltage	$V_S$	$V_B-20$	$V_B$	
High side floating output voltage	$V_{HO}$	$V_S$	$V_B$	
Low side and logic fixed supply voltage	$V_{CC}$	10	20	
Low side output voltage	$V_{LO}$	0	$V_{CC}$	
Input voltage LIN, HIN, ITRIP, EN	$V_{IN}$	0	$V_{CC}$	
RCIN input voltage	$V_{RCIN}$	$V_{SS}$	$V_{CC}$	
FAULTB output voltage	$V_{FLT}$	$V_{SS}$	$V_{CC}$	

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#### Static Electrical Characteristics

V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>B1,2,3</sub>) = 15 V unless otherwise specified. The V<sub>IN</sub>, V<sub>TH</sub>, and I<sub>IN</sub> parameters are referenced to V<sub>SS</sub> and are applicable to all six channels (HIN1,2,3 and LIN1,2,3). The V<sub>O</sub> and I<sub>O</sub> parameters are referenced to COM and V<sub>S1,2,3</sub> and are applicable to the respective output leads: HO1,2,3 and LO1,2,3.

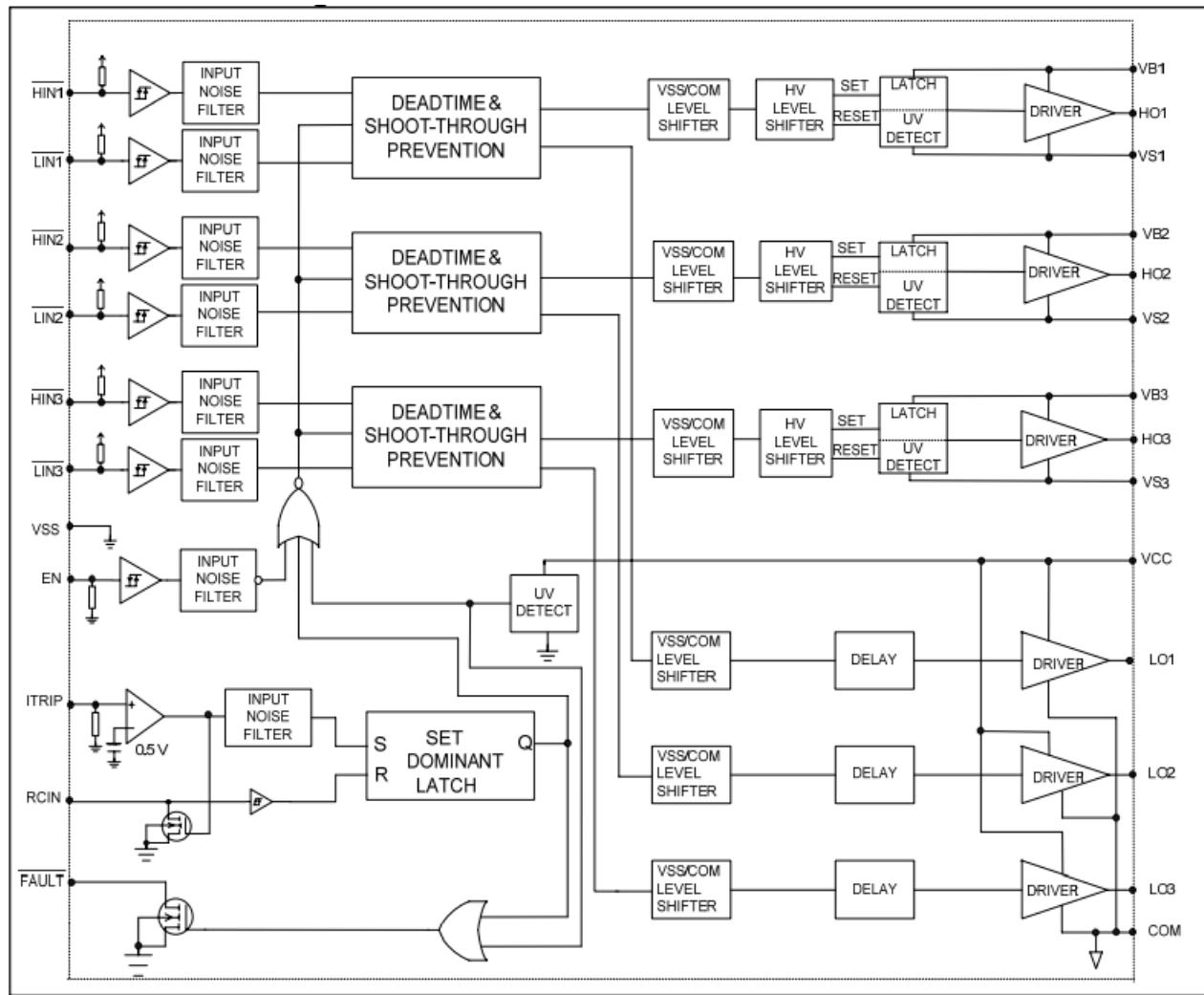
Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Low Side Power Supply</b>					
V <sub>CC</sub> quiescent current	I <sub>QVCC</sub>	/HIN1,2,3=0 or 5V /LIN1,2,3=0 or 5V		750 1500	uA
V <sub>CC</sub> UVLO rising threshold	V <sub>CCUVR</sub>		8.0	8.9 9.8	V
V <sub>CC</sub> UVLO falling threshold	V <sub>CCUVF</sub>		7.3	8.2 9.0	V
V <sub>CC</sub> UVLO hysteresis	V <sub>CCUVH</sub>			0.7	V
<b>High Side Floating Power Supply</b>					
High Side V <sub>BS</sub> quiescent current	I <sub>QBS</sub>	V <sub>BS</sub> =15V		60 120	uA
Offset supply leakage current	I <sub>LK</sub>	V <sub>B</sub> =V <sub>S</sub> =600V, V <sub>CC</sub> =0		0.1 50	uA
V <sub>BS</sub> UVLO rising threshold	V <sub>BSUVR</sub>		7.7	8.6 9.5	V
V <sub>BS</sub> UVLO falling threshold	V <sub>BSUVF</sub>		7.0	7.8 8.7	V
V <sub>BS</sub> UVLO hysteresis	V <sub>BSUVH</sub>			0.8	V
<b>Gate Driver Output</b>					
Output Source current	I <sub>OSRC</sub>	V <sub>O</sub> =0, V <sub>IN</sub> =5V, PW ≤10us		300	mA
Output Sink current	I <sub>OSIK</sub>	V <sub>O</sub> =15V, V <sub>IN</sub> =0V, PW ≤10us		600	mA
High level output voltage drop	V <sub>OH</sub>	I <sub>O</sub> =20mA		800 1500	mV
Low level output voltage drop	V <sub>OL</sub>	I <sub>O</sub> =20mA		300 500	mV
Negative voltage of output	V <sub>NG</sub>			-10	V
<b>Logic Input</b>					
Logic"1" input voltage of /HIN1,2,3 and /LIN1,2,3	V <sub>IH</sub>		2.5		V
Logic"0" input voltage of /HIN1,2,3 and /LIN1,2,3	V <sub>IL</sub>			0.8	V
Logic"1" input bias current	I <sub>IH</sub>	V <sub>O</sub> =0, V <sub>IN</sub> =5V		0	uA
Logic"0" input bias current	I <sub>IL</sub>	V <sub>O</sub> =15V, V <sub>IN</sub> =0V		100 200	uA

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**Static Electrical Characteristics**

Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Shutdown and protection</b>					
RCIN positive going threshold	$V_{RCINR}$		8.0		V
RCIN hysteresis	$V_{RCINH}$		3.0		V
RCIN pull down MOSFET	$R_{RCIN}$	$I_{SINK}=2\text{mA}$	30	50	$\Omega$
ITRIP positive going threshold	$V_{ITRIPR}$		350	450	550
ITRIP hysteresis	$V_{ITRIPH}$		40	70	mV
EN rising threshold	$V_{ENR}$		2.5		V
EN falling threshold	$V_{ENF}$			0.8	V
High enable input bias current	$I_{ENH}$		60	120	uA
Low enable input bias current	$I_{ENL}$		0		uA
/FAULT on resistance	$R_{ON\_FLT}$	$I_{SINK}=2\text{mA}$	30	50	$\Omega$
<b>Timing</b>					
Turn on propagation delay	$t_{ON}$	$V_{CC}=15\text{V}, V_{BS}=15\text{V}, C_L=1\text{nF}$	425	550	ns
Turn off propagation delay	$t_{OFF}$		425	550	ns
Turn on Rise time	$t_R$		125	190	ns
Turn on Fall time	$t_F$		50	75	ns
Input filter time	$t_{FLTIN}$		350		ns
Enable low to output shutdown propagation delay	$t_{EN}$		450	600	ns
ITRIP to output shutdown propagation delay	$t_{ITRIP}$		750	1000	ns
ITRIP blanking time	$t_{BL}$		350		ns
ITRIP to /FAULT propagation delay	$t_{FLT}$		650	900	ns
FAULT clear time RCIN	$t_{FLTCLR}$	$R=2M\Omega, C=1\text{nF}$	1.75	2.0	ms
Dead time	DT		200	290	380
Matching delay ON and OFF	MT		20	75	ns
Output pulse width matching	PM		40	75	ns

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### Function Block Diagram



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### Timing Diagram

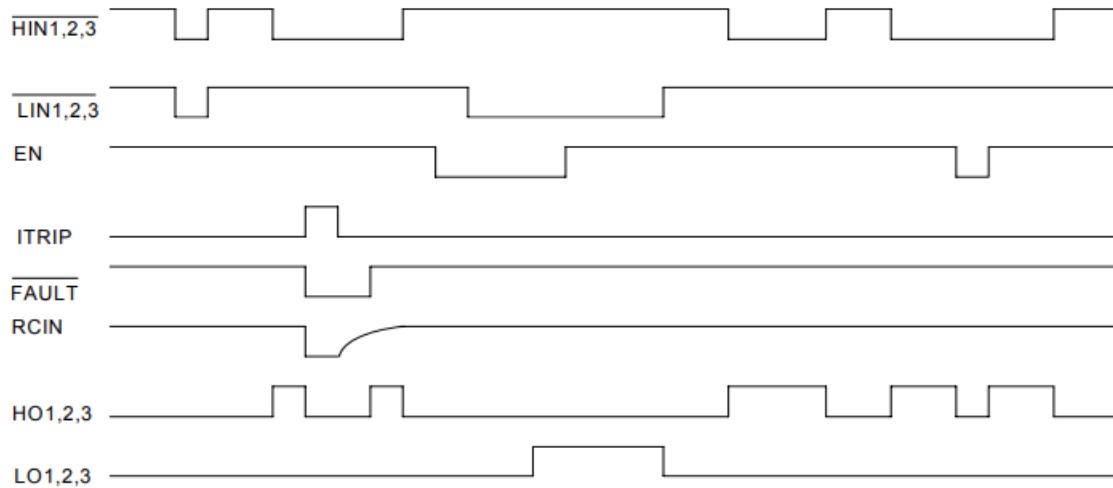


Fig1. Input/Output Timing Diagram

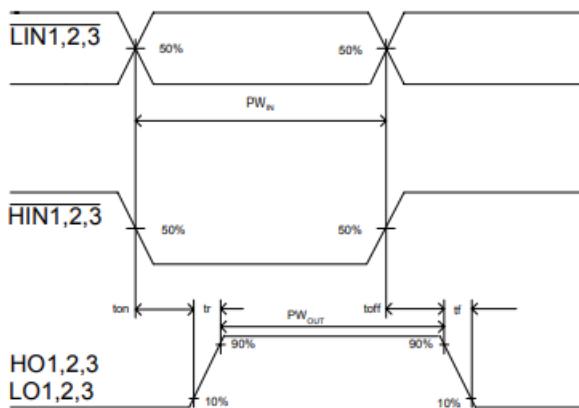


Fig2. Switching time

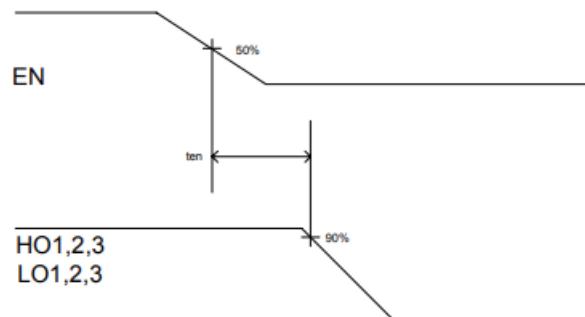


Fig3. Output Enable timing

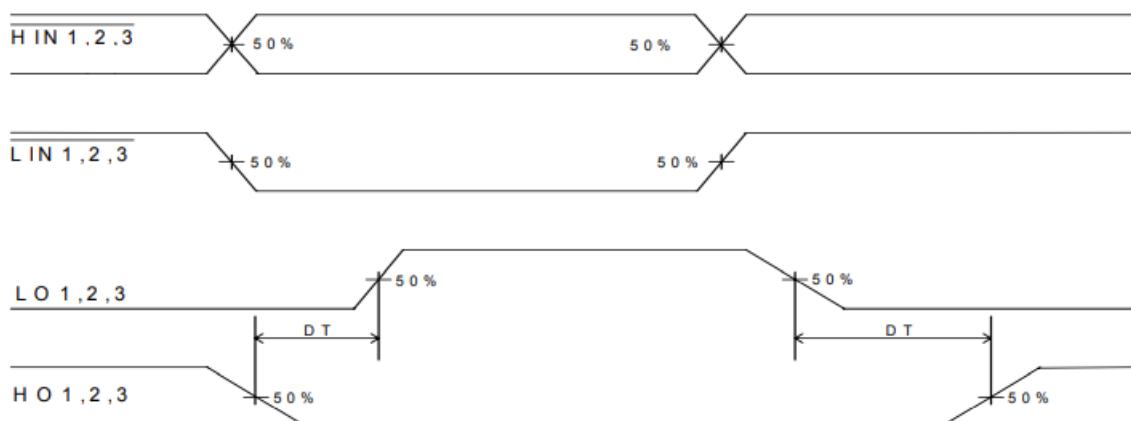


Fig4. Internal Deadtime timing

### 3-Phase 600V Gate Driver IC

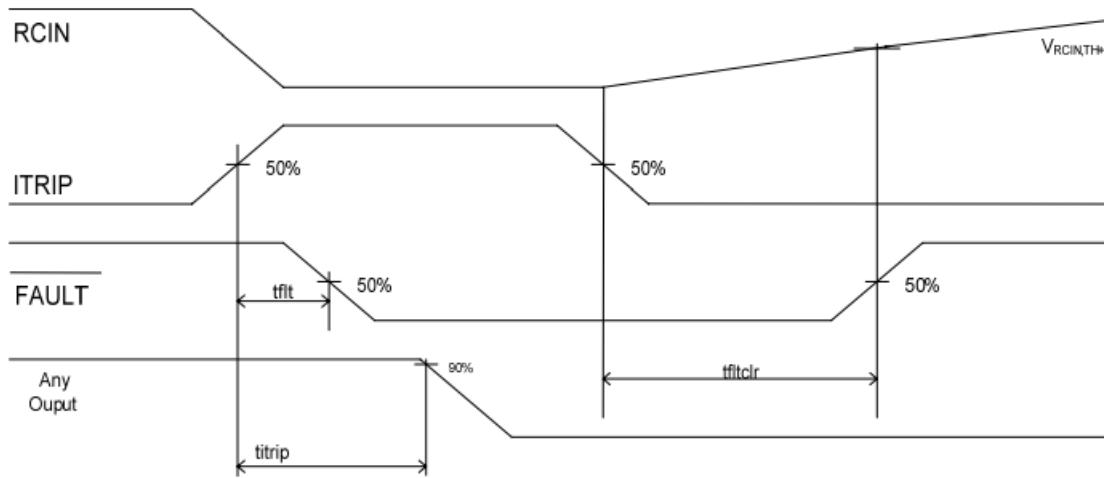


Fig5. IRTIP/RCIN timing

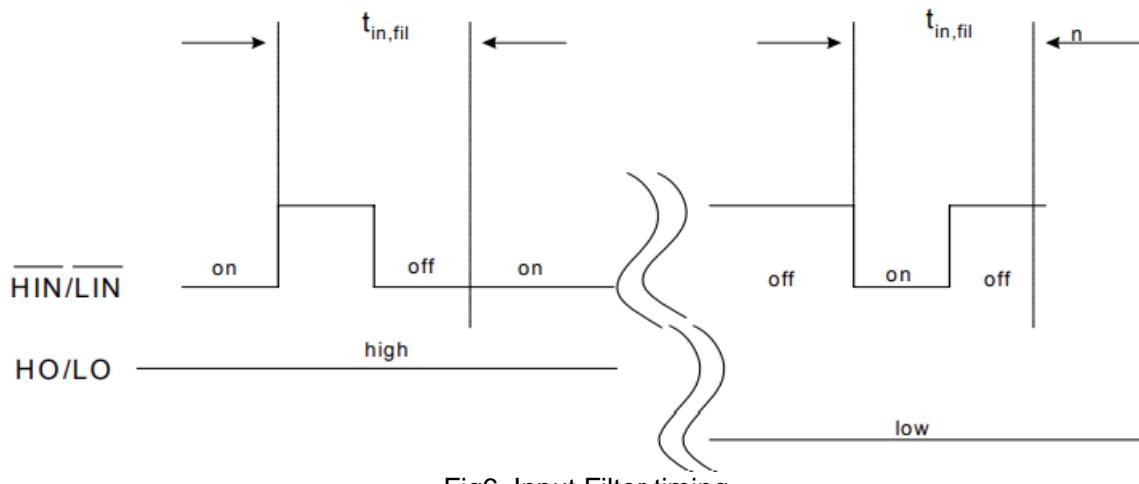
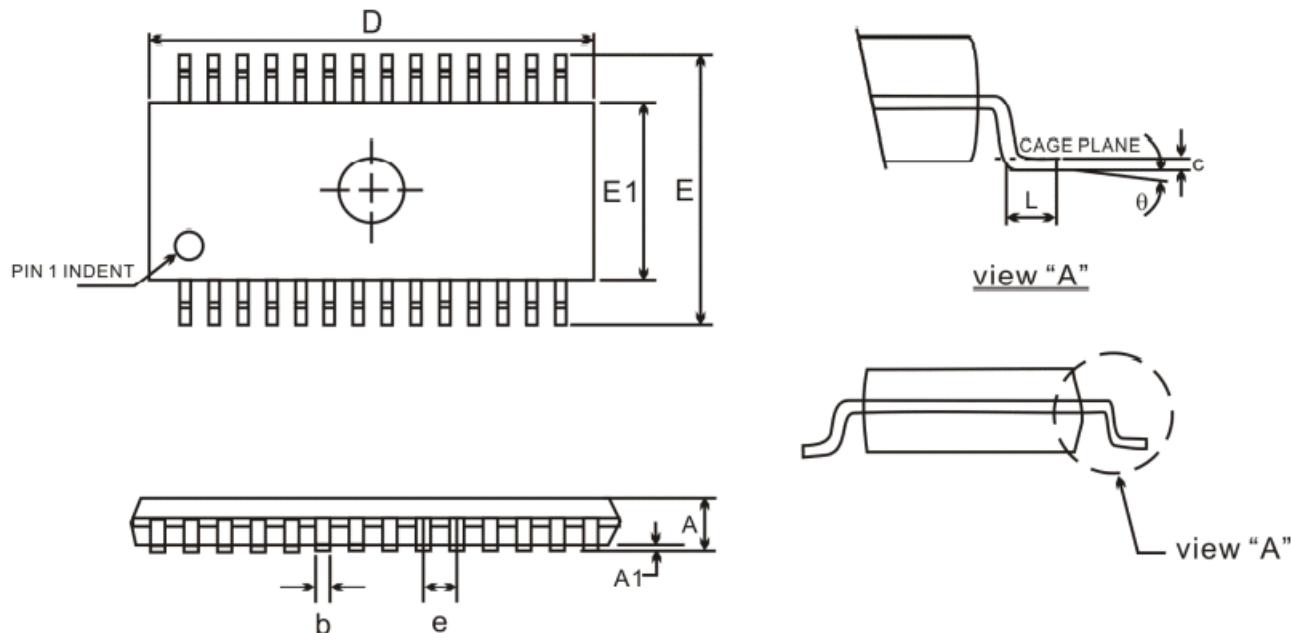


Fig6. Input Filter timing

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### Package Information SOP28



Symbol	Min.	Typ.	Max.
A	-	-	2.65
A1	0.10	-	0.30
b	0.31	-	0.51
c	0.20	-	0.33
e		1.27 BSC.	
D		17.90 BSC.	
E		10.30 BSC.	
E1		7.50 BSC.	
L	0.38	-	1.27
θ	0°	-	8°

Notes:

1. All controlling dimensions are in millimeter.
2. Refer to JEDEC MS-013 AD.

## **3-Phase 600V Gate Driver IC**

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